



## Supporting Information

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Crossbreeding Effect of Chalcogenation and Iodination on Benzene Additives Enables Optimized Morphology and 19.68% Efficiency of Organic Solar Cells

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**1. Materials and Methods**

**Materials:** PM6 was purchased from Solarmer Materials Inc. L8-BO was purchased from Vizuchem Inc. PBTz-F was prepared by our group.<sup>[1]</sup> All the other chemicals were purchased from Aladdin, Adamas, Sigma-Aldrich and Alfa Aesar Chemical Co., and used without further purification.

**Methods:** Thermogravimetric analysis (TGA) was conducted on a TA Instrument Model SDT Q500 at a heating rate of 10 °C min<sup>-1</sup> and under a N<sub>2</sub> flow rate of 90 mL min<sup>-1</sup>. UV-vis-NIR spectra were obtained on a Shimadzu UV3600 spectrophotometer. <sup>1</sup>H NMR was record from

a JNM-ECZ400S nuclear magnetic resonance spectrometer using  $\text{CDCl}_3$  as the solvent. GIWAXS measurements were performed at Complex Materials Scattering (CMS) beamline of the National Synchrotron Light Source II (NSLS-II), Brookhaven National Lab. AFM images were obtained by using a Bruker Inova atomic microscope in tapping mode. TEM images were obtained by using a Thermo Scientific Talos F200S G2 transmission electron microscope. Femtosecond transient absorption (fs-TA) spectroscopy experiments were performed using a home-built system with a Ti: sapphire regenerative amplified laser system (Coherent Legend Elite). The probe beam was generated by focusing part of the fundamental femtosecond laser beam onto a 3-mm-thick sapphire plate or 4 mm-thick Yttrium aluminum garnet plate for visible (vis) and near-IR (NIR) spectral windows, respectively. 780 nm laser was used to selectively excite NFAs. TA results in this work were presented in the unit of  $\Delta\text{OD}$ , negative features could reflect ground-state bleaching (GSB) or stimulated emission (SE), a positive signal was an excited-state absorption (ESA). During TA measurements, the samples were kept in nitrogen to avoid photodegradation. The pump fluence was kept at  $<5 \mu\text{J cm}^{-2}$  to minimize the exciton–exciton annihilation effect.

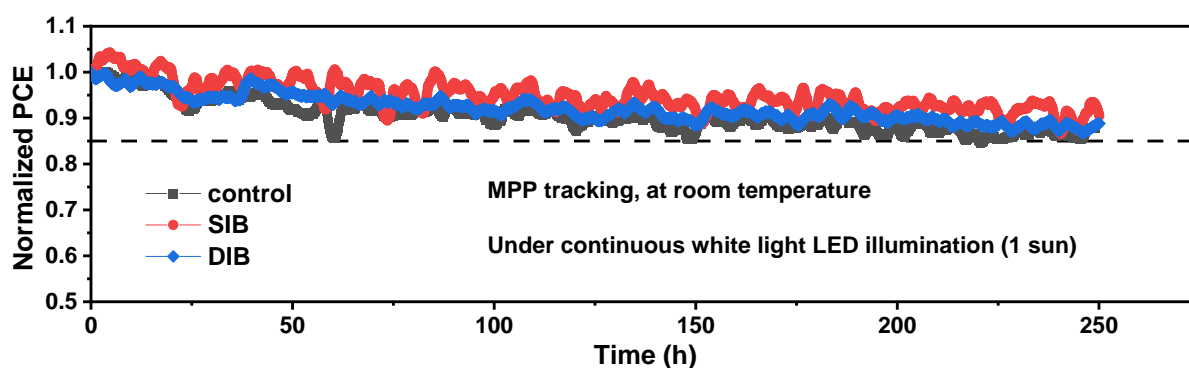
## 2. Device Fabrication and Measurements

**Device fabrication:** The patterned indium tin oxide (ITO, sheet resistance =  $15 \Omega \text{ square}^{-1}$ ) glass substrates were sequentially ultrasonicated with detergent, deionized water, acetone and isopropanol. Then, the ITO glasses were treated with UV-ozone for 30 min. Poly(3,4-ethylenedioxythiophene):polystyrene sulfonate (PEDOT:PSS) (Bay PVP. Al 4083, Bayer AG) was filtrated through a  $0.45 \mu\text{m}$  nylon filter and then spin-coated on the cleaned ITO substrates at 5000 rpm for 60 s to form a thin layer (35 nm). After that, the substrates were baked at  $150^\circ\text{C}$  on a hot plate for 10 min. The PM6:L8-BO solutions (1:1.2 by weight, 16.5 mg/mL in chloroform) or PBTz-F:PM6:L8-BO solutions ( $x:(1-x):1.2$  by weight, 16.5 mg/mL in chloroform) without and with different additives were stirred at room temperature for 2

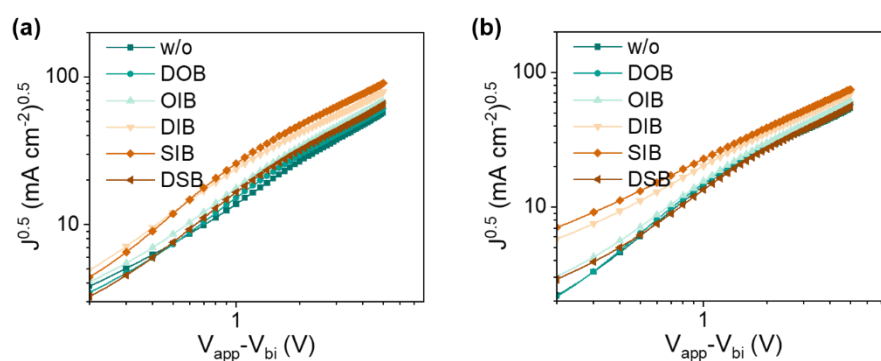
hours before used. The above solutions were spin-coated on the ITO/PEDOT:PSS substrates at a speed of 3000 rpm for 30 s to form a ~100 nm thickness of the photoactive layer. Then, the substrates were baked at 100 °C for 10 min. PNDIT-F3N solution (0.5 mg/mL in methanol with 5 v% of acetic acid) was spin-coated on the top of the active layer to form a thin cathode interlayer. Finally, argentum electrode (Ag, 100 nm) was deposited under high vacuum ( $\sim 10^{-5}$  Pa) in an evaporation chamber. For the hole-only devices, after deposition of the photoactive layer on ITO/PEDOT:PSS substrates, molybdenum oxide (10 nm) and Ag electrode (100 nm) were deposited under high vacuum ( $\sim 10^{-5}$  Pa) in an evaporation chamber. For the electron-only devices, diethylzinc solution (2 M in toluene diluted by tetrahydrofuran) was spin-coated on the ITO substrates under dry air followed by baked at 200 °C for 30 min, the other fabrication processes were identical to the OSC devices.

**Device measurements:** The  $I$ - $V$  characterization was performed on a computer-controlled Keithley 2400 Source under AM1.5G ( $100 \text{ mW cm}^{-2}$ ) using a solar simulator (XES-70S1, SAN-EI), which was calibrated by a standard Si solar cell (AK-200, Konica Minolta, Inc.). The EQE values were measured with an EQ-R solar quantum efficiency test system (Enlitech Co., Ltd., Taiwan, China). All fabrication and characterization processes, except for the HTLs preparation and EQE measurements, were conducted in a high purity argon filled glove box.

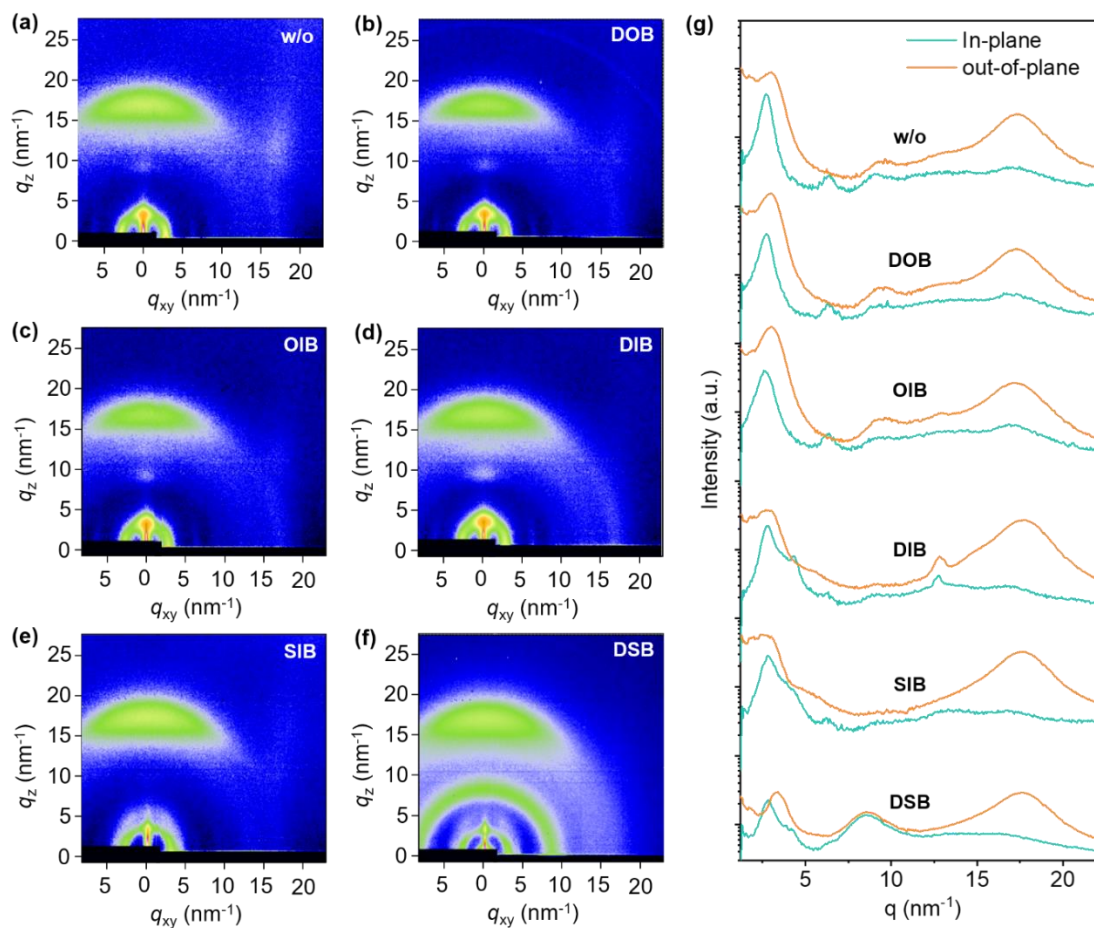
### 3. Supplementary Figures



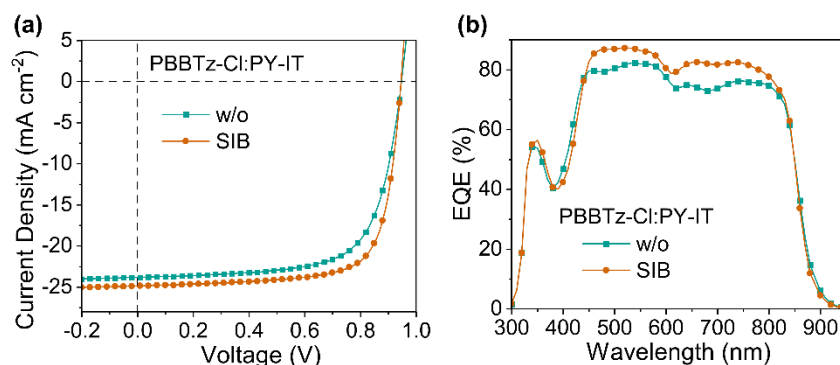
**Figure S1.** Normalized PCEs of the devices without additive and with SIB, DIB additive, respectively, under continuous white light LED illumination.



**Figure S2.**  $J^{0.5}$ - $V$  curves of the (a) hole-only and (b) electron-only devices.



**Figure S3.** a-f) GIWAXS patterns of PM6 films modified with various additives. g) The corresponding in-plane and out-of-plane line-cuts from (a-f).



**Figure S4.** a)  $J$ - $V$  curves of the PBBTz-Cl:PY-IT based all-PSCs without and with SIB additive modification. c) EQE spectra of the PBBTz-Cl:PY-IT based all-PSCs without and with SIB additive modification.

### 3. Supplementary Tables

**Table S1.** Charge carrier mobilities of the PM6:L8-BO blends with various additives.

Additive	$\mu_h$ [cm <sup>2</sup> V <sup>-1</sup> s <sup>-1</sup> ]	$\mu_e$ [cm <sup>2</sup> V <sup>-1</sup> s <sup>-1</sup> ]
w/o	$3.3 \times 10^{-4}$	$2.4 \times 10^{-4}$
DOB	$3.5 \times 10^{-4}$	$2.9 \times 10^{-4}$
OIB	$4.3 \times 10^{-4}$	$3.5 \times 10^{-4}$
DIB	$4.7 \times 10^{-4}$	$4.1 \times 10^{-4}$
SIB	$5.1 \times 10^{-4}$	$4.5 \times 10^{-4}$
DSB	$3.8 \times 10^{-4}$	$2.8 \times 10^{-5}$

**Table S2.** Summarized parameters for the ordered structures of L8-BO with various additives

Additive	Lamellar stacking			$\pi$ - $\pi$ stacking		
	q/d	FWHM	CCL	q/d	FWHM	CCL
	[nm <sup>-1</sup> ]/[nm]	[nm <sup>-1</sup> ]	[nm]	[nm <sup>-1</sup> ]/[nm]	[nm <sup>-1</sup> ]	[nm]
w/o	4.08/1.51	1.39	6.07	17.8/0.353	3.39	2.50
DOB	4.10/1.51	1.37	6.16	17.8/0.353	3.16	2.68
OIB	4.06/1.55	1.07	7.89	17.9/0.351	3.02	2.81
DIB	3.36/1.87	0.786	10.7	18.0/0.349	2.65	3.20
	4.30/1.46	0.807	10.4			
SIB	3.39/1.85	0.326	25.9	18.0/0.349	2.05	4.14
	4.48/1.41	0.539	15.7			
DSB	4.05/1.55	0.204	41.4	17.5/0.359	1.11	7.65

**Table S3.** Photovoltaic parameters of PBBTz-Cl:PY-IT based all-PSCs without and with SIB additive.

SIB	$V_{oc}$ [V]	$J_{sc}$ [mA cm <sup>-2</sup> ]	$J_{EQE}^{b)}$ [mA cm <sup>-2</sup> ]	FF [%]	PCE [%]
w/o	0.948	23.82	23.17	69.23	15.63
	0.951±0.002 <sup>a)</sup>	23.72±0.31		67.91±0.75	15.32±0.27
50 wt%	0.946	24.87	24.66	74.23	17.47
	0.952±0.005	24.37±0.51		74.12±0.60	17.19±0.42

<sup>a)</sup>The averaged values with standard deviations were calculated from 10 individual devices; <sup>b)</sup>The integrated current densities were calculated from the EQE curves.

**Table S4.** Photovoltaic parameters of PM6:PBTz-F:L8-BO based OSCs with different weight ratios of PM6:PBTz-F.

PM6:PBTz-F	$V_{oc}$ [V]	$J_{sc}$ [mA cm <sup>-2</sup> ]	$J_{EQE}^{b)}$ [mA cm <sup>-2</sup> ]	FF [%]	PCE [%]
1:0	0.898	26.30	25.46	79.92	18.87
	0.896±0.005 <sup>a)</sup>	26.27±0.19		78.96±0.91	18.58±0.24
0.8:0.2	0.907	27.10	25.90	80.06	19.68
	0.906±0.005	26.93±0.13		78.96±0.77	19.27±0.23
0.7:0.3	0.909	26.91	25.82	79.22	19.37
	0.901±0.007	26.87±0.14		78.69±0.87	19.05±0.31
0:1	0.905	26.57	25.55	78.23	18.81
	0.908±0.005	26.31±0.27		77.56±0.59	18.53±0.29

<sup>a)</sup>The averaged values with standard deviations were calculated from 10 individual devices; <sup>b)</sup>The integrated current densities were calculated from the EQE curves.

## References

- [1] B. Pang, C. Liao, X. Xu, L. Yu, R. Li, Q. Peng, *Adv. Mater.* **2023**, 35, 2300631.